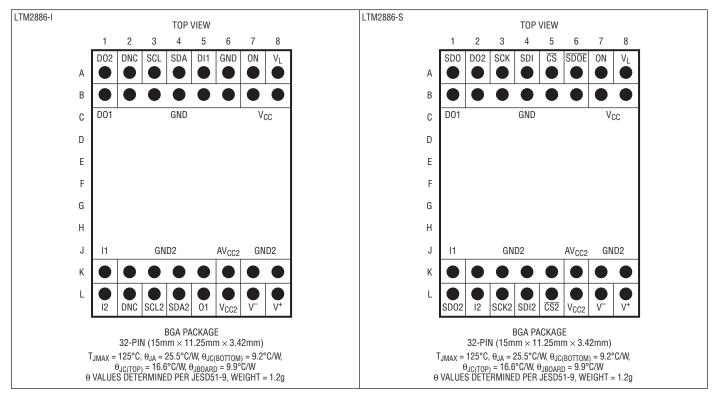
ABSOLUTE MAXIMUM RATINGS

(Note 1)

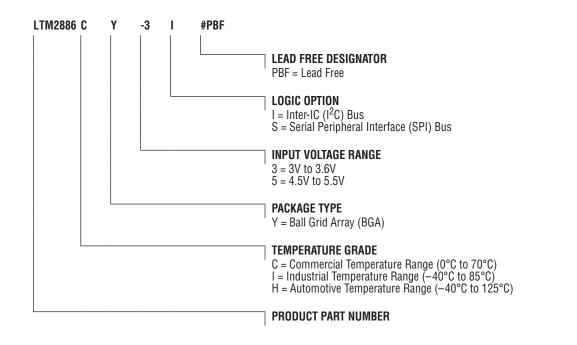
V _{CC} to GND	0.3V to 6V
V _L to GND	–0.3V to 6V
V _{CC2} , AV _{CC2} to GND2	0.3V to 6V
V ⁺ to GND2	–0.3V to 6V
V ⁻ to GND2	0.3V to -6V
Logic Inputs	
DI1, SCK, SDI, CS, SCL, SD	A, <u>SDOE</u> ,
ON to GND	–0.3V to (V _L + 0.3V)
I1, I2, SDA2,	
SDO2 to GND2	0.3V to (V _{CC2} + 0.3V)

Logic Outputs D01, D02, SD0 to GND0.3V to $(V_L + 0.3V)$ 01, SCK2, SDI2, CS2,
SCL2 to GND20.3V to $(V_{CC2} + 0.3V)$
Operating Temperature Range (Note 4)
LTM2886C 0°C to 70°C
LTM2886I40°C to 85°C
LTM2886H40°C to 125°C
Maximum Internal Operating Temperature 125°C
Storage Temperature Range –55°C to 125°C
Peak Body Reflow Temperature

PIN CONFIGURATION



PRODUCT SELECTION GUIDE



ORDER INFORMATION http://www.linear.com/product/LTM2886#orderinfo

	PART MARKING							
PART NUMBER	PAD OR BALL Finish	DEVICE	FINISH CODE	PACKAGE Type	MSL Rating	INPUT VOLTAGE Range	LOGIC Option	TEMPERATURE RANGE
LTM2886CY-3I#PBF								0°C to 70°C
LTM2886IY-3I#PBF		LTM2886Y-3I					I ² C	-40°C to 85°C
LTM2886HY-3I#PBF						3V to 3.6V		-40°C to 125°C
LTM2886CY-3S#PBF						50 10 5.00	SPI	0°C to 70°C
LTM2886IY-3S#PBF	l	LTM2886Y-3S						-40°C to 85°C
LTM2886HY-3S#PBF			at	DCA				-40°C to 125°C
LTM2886CY-5I#PBF	SAC305 (RoHS)		e1	e1 BGA 3	3		l ² C	0°C to 70°C
LTM2886IY-5I#PBF		LTM2886Y-51						–40°C to 85°C
LTM2886HY-5I#PBF								-40°C to 125°C
LTM2886CY-5S#PBF						4.5V to 5.5V		0°C to 70°C
LTM2886IY-5S#PBF		LTM2886Y-5S					SPI	-40°C to 85°C
LTM2886HY-5S#PBF								-40°C to 125°C

• Device temperature grade is indicated by a label on the shipping container.

 Recommended BGA PCB Assembly and Manufacturing Procedures: www.linear. com/BGA-assy

Pad or ball finish code is per IPC/JEDEC J-STD-609.
Terminal Finish Part Marking: www.linear.com/leadfree

BGA Package and Tray Drawings: www.linear.com/packaging

• This product is not recommended for second side reflow. For more information, go to www.linear.com/BGA-assy

• This product is moisture sensitive. For more information, go to: www.linear.com/BGA-assy

ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the specified operating temperature range, otherwise specifications are at T_A = 25°C. LTM2886-3 V_{CC} = 3.3V, LTM2886-5 V_{CC} = 5V, V_L = 3.3V, and GND = GND2 = 0V, ON = V_L unless otherwise noted. Specifications apply to all options unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	ТҮР	MAX	UNITS
Input Sup	plies						
V _{CC}	Input Supply Range	LTM2886-3 LTM2886-5	•	3 4.5	3.3 5	3.6 5.5	V V
VL	Logic Supply Range	LTM2886-S LTM2886-I	•	1.62 3	5	5.5 5.5	V V
I _{CC}	Input Supply Current	ON = 0V LTM2886-3, No Load LTM2886-5, No Load	•		0 25 19	10 37 27	μA mA mA
IL	Logic Supply Current	ON = OV LTM2886-S, $ON = V_L$ LTM2886-I, $ON = V_L$	•		0 10	10 150	μΑ μΑ μΑ
Output Si	upplies	1					
V _{CC2}	Regulated Output Voltage	No Load, AV _{CC2} OPEN	•	4.75	5	5.25	V
	Output Voltage Operating Range	(Note 2)		3		5.5	V
	Line Regulation	$I_{LOAD} = 1$ mA, MIN $\leq V_{CC} \leq MAX$	•		2	7.5	mV
	Load Regulation	I _{LOAD} = 1mA to 100mA	•		15	100	mV
	ADJ Pin Voltage	I _{LOAD} = 1mA to 100mA	•	1.15	1.220	1.27	V
	Voltage Ripple	I _{LOAD} = 100mA (Note 2)			1		mV _{RMS}
	Efficiency	LTM2886-5, I _{LOAD} = 100mA (Note 2)			61		%
I _{CC2}	Output Short Circuit Current	V _{CC2} = 0V			150		mA
	Current Limit	$\Delta V_{CC2} = -5\%$	•	90			mA
V ⁺	Regulated Output Voltage	No Load	•	4.8	5	5.2	V
	Line Regulation	$I_{LOAD} = 1$ mA, MIN $\leq V_{CC} \leq$ MAX	•		2	7.5	mV
	Load Regulation	I _{LOAD} = 1mA to 100mA	•		35	150	mV
	Voltage Ripple	I _{LOAD} = 100mA (Note 2)			1		mV _{RMS}
	Efficiency	LTM2886-5, I _{LOAD} = 100mA (Note 2)			61		%
+	Output Short Circuit Current	V ⁺ = 0V			150		mA
	Current Limit	$\Delta V^{+} = -5\%$	•	90			mA
V-	Regulated Output Voltage	No Load	•	-4.8	-5	-5.2	V
	Line Regulation	$I_{LOAD} = -1$ mA, MIN $\leq V_{CC} \leq$ MAX	•		5	15	mV
	Load Regulation	I _{LOAD} = 1mA to 100mA	•		35	150	mV
	Voltage Ripple	I _{LOAD} = 100mA (Note 2)			1		mV _{RMS}
	Efficiency	LTM2886-5, I _{LOAD} = 100mA (Note 2)			61		%
I [_]	Output Short-Circuit Current	V ⁻ = 0V			150		mA
	Current Limit	$\Delta V^{-} = 5\%$	•	90			mA

ELECTRICAL CHARACTERISTICS The • denotes the specifications which apply over the specified operating temperature range, otherwise specifications are at $T_A = 25$ °C. LTM2886-3 V_{CC} = 3.3V, LTM2886-5 V_{CC} = 5V, V_L = 3.3V, and GND = GND2 = 0V, ON = V_L unless otherwise noted. Specifications apply to all options unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	ТҮР	MAX	UNITS
Logic/SP	1	,					
V _{ITH}	Input Threshold Voltage	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	•	0.25 • V _L 0.33 • V _L 0.33 • V _{CC2}		0.75 • V _L 0.67 • V _L 0.67 • V _{CC2}	V V V
I _{INL}	Input Current					±1	μA
V _{HYS}	Input Hysteresis				150		mV
V _{OH}	Output High Voltage	D01, D02, SD0, $\begin{split} I_{LOAD} &= -1mA, \ 1.62V \leq V_L < 3V, \\ I_{LOAD} &= -4mA, \ 3V \leq V_L \leq 5.5V \end{split}$	•	V _L - 0.4			V
		01, SCK2, SDI2, $\overline{CS2}$, $I_{LOAD} = -4mA$	•	V _{CC2} - 0.4			V
V _{OL}	Output Low Voltage	D01, D02, SD0, $\begin{split} I_{LOAD} &= 1 m A, \ 1.62 V \leq V_L < 3 V, \\ I_{LOAD} &= 4 m A, \ 3 V \leq V_L \leq 5.5 V \end{split}$	•			0.4	V
		01, SCK2, SDI2, $\overline{CS2}$, $I_{LOAD} = 4mA$	•			0.4	V
I _{SC}	Short-Circuit Current	$\begin{array}{l} \text{OV} \leq (\text{D01, D02, SD0}) \leq \underline{V_L} \\ \text{OV} \leq (\text{O1, SCK2, SD12, CS2}) \leq V_{\text{CC2}} \end{array}$	•		±60	±85	mA mA
l ² C							
V _{IL}	Low Level Input Voltage	SCL, SDA SDA2	•			0.3 • V _L 0.3 • V _{CC2}	V V
V _{IH}	High Level Input Voltage	SCL, SDA SDA2	•	0.7 • V _L 0.7 • V _{CC2}			V V
I _{INL}	Input Current	SCL, SDA = V_L or 0V SDA2 = V_{CC2} , SDA2 = V_{CC2} = 0V	•			±1 ±1	μA μA
V _{HYS}	Input Hysteresis	SCL, SDA SDA2			0.05 • V _L 0.05 • V _{CC2}		V V
V _{OH}	Output High Voltage	SCL2, $I_{LOAD} = -2mA$ DO2, $I_{LOAD} = -2mA$	•	$V_{CC2} - 0.4 V_L - 0.4$			V V
V _{OL}	Output Low Voltage	SDA, $I_{LOAD} = 3mA$ D02, $I_{LOAD} = 2mA$ SCL2, $I_{LOAD} = 2mA$ SDA2, No Load, SDA = 0V, $4.5V \le V_{CC2} < 5.5V$ SDA2, No Load, SDA = 0V, $3V \le V_{CC2} < 4.5V$	• • •		0.3	0.4 0.4 0.45 0.55	V V V V V
CIN	Input Pin Capacitance	SCL, SDA, SDA2 (Note 2)	•			10	pF
C _B	Bus Capacitive Load	$\begin{array}{l} SCL2, Standard Speed (Note 2)\\ SCL2, Fast Speed\\ SDA, SDA2, SR \geq 1V/\mu s, Standard Speed (Note 2)\\ SDA, SDA2, SR \geq 1V/\mu s, Fast Speed\\ \end{array}$	• • •			400 200 400 200	pF pF pF pF
	Minimum Bus Slew Rate	SDA, SDA2	•	1			V/µs
I _{SC}	Short-Circuit Current	$\begin{array}{l} SDA2 = 0, SDA = V_L\\ 0V \leq SCL2 \leq V_{CC2}\\ 0V \leq D02 \leq V_L\\ SDA = 0, SDA2 = V_{CC2}\\ SDA = V_L, SDA2 = 0 \end{array}$	•		±30 ±30 6 -1.8	100	mA mA mA mA mA
ESD (HB	M) (Note 2)						
	Isolation Boundary	$(V_{CC2}, V^+, V^-, GND2)$ to (V_{CC}, V_L, GND)			±10		kV

SWITCHING CHARACTERISTICS The \bullet denotes the specifications which apply over the specified operating temperature range, otherwise specifications are at T_A = 25°C. LTM2886-3 V_{CC} = 3.3V, LTM2886-5 V_{CC} = 5V, V_L = 3.3V, and GND = GND2 = 0V, ON = V_L unless otherwise noted. Specifications apply to all options unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	ТҮР	MAX	UNITS
Logic		l	I				
	Maximum Data Rate	$DI1 \rightarrow 01$, $Ix \rightarrow DOx$, $C_L = 15pF$ (Note 3)		10			MHz
t _{PHL} , t _{PLH}	Propagation Delay	C _L = 15pF (Figure 1)		35	60	100	ns
t _R	Rise Time	C _L = 15pF (Figure 1) LTM2886-I, DO2, C _L = 15pF (Figure 1)	•		3 20	12.5 35	ns ns
t _F	Fall Time	C _L = 15pF (Figure 1) LTM2886-I, DO2, C _L = 15pF (Figure 1)	•		3 20	12.5 35	ns ns
SPI							
	Maximum Data Rate	Bidirectional Communication (Note 3) Unidirectional Communication (Note 3)	•	4 8			MHz MHz
t _{PHL} , t _{PLH}	Propagation Delay	C _L = 15pF (Figure 1)		35	60	100	ns
t _{PWU}	Output Pulse Width Uncertainty	SDO, SDI2, CS2 (Note 2)				±50	ns
t _R	Rise Time	$C_L = 15pF$ (Figure 1)			3	12.5	ns
t _F	Fall Time	$C_L = 15 pF$ (Figure 1)			3	12.5	ns
t _{PZH,} t _{PZL}	Output Enable Time	$\overline{\text{SDOE}} = \downarrow$, R _L = 1k Ω , C _L = 15pF (Figure 2)				50	ns
t _{PHZ,} t _{PLZ}	Output Disable Time	$\overline{\text{SDOE}} = \uparrow$, R _L = 1k Ω , C _L = 15pF (Figure 2)				50	ns
l ² C							
	Maximum Data Rate	(Note 3)		400			kHz
t _{PHL} , t _{PLH}	Propagation Delay	$SCL \rightarrow SCL2, C_L = 15pF$ (Figure 1) $SDA \rightarrow SDA2, R_L = Open, C_L = 15pF$ (Figure 3) $SDA2 \rightarrow SDA, R_L = 1.1k\Omega, C_L = 15pF$ (Figure 3)	•		150 150 300	225 250 500	ns ns ns
t _{PWU}	Output Pulse Width Uncertainty	SDA, SDA2 (Note 2)				±50	ns
t _{HD;DAT}	Data Hold Time	(Note 2)			600		ns
t _R	Rise Time	SDA2, $C_L = 200pF$ (Figure 3) SDA, $R_L = 1.1k\Omega C_L = 200pF$ (Figure 3) SCL2, $C_L = 200pF$ (Figure 1)	•	40 40		300 250 250	ns ns ns
t _F	Fall Time	SDA2, $C_L = 200pF$ (Figure 3) SDA, $R_L = 1.1k\Omega$ $C_L = 200pF$ (Figure 3) SCL2, $C_L = 200pF$ (Figure 1)	•	40 40		250 250 250	ns ns ns
t _{SP}	Pulse Width of Spikes Suppressed by Input Filter		•	0		50	ns
Power Su	pply						_ <u>.</u>
	Power-Up Time	$ \begin{array}{ c c } ON = \uparrow \mbox{ to } V_{CC2} \mbox{ (Min)} \\ ON = \uparrow \mbox{ to } V^+ \mbox{ (Min)} \\ ON = \uparrow \mbox{ to } V^- \mbox{ (Min)} \\ \end{array} $	•		0.6 0.6 0.6	5 5 5	ms ms ms

ISOLATION CHARACTERISTICS $T_A = 25 \degree C$.

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNITS
V _{ISO}	Rated Dielectric Insulation Voltage	1 Minute, Derived from 1 Second Test 1 Second (Notes 5, 6)	2500 3000			V _{RMS} V _{RMS}
	Common Mode Transient Immunity	LTM2886-3 V _{CC} = 3.3V, LTM2885-5 V _{CC} = 5V, V _L = 0N = 3.3V, V _{CM} = 1kV, Δt = 33ns (Note 2)	30			kV/µs
V _{IORM} Maximu	Maximum Continuous Working Voltage	(Notes 2, 5)	560			V _{PEAK} ,
			400			V _{DC} V _{RMS}
	Partial Discharge	V _{PD} = 750V _{RMS} (Note 5)			5	pC
CTI	Comparative Tracking Index	IEC 60112 (Note 2)	600			V _{RMS}
	Depth of Erosion	IEC 60112 (Note 2)		0.017		mm
DTI	Distance Through Insulation	(Note 2)		0.06		mm
	Input to Output Resistance	(Notes 2, 5)	10 ⁹			Ω
	Input to Output Capacitance	(Notes 2, 5)		6		pF
	Creepage Distance	(Note 2)		9.5		mm

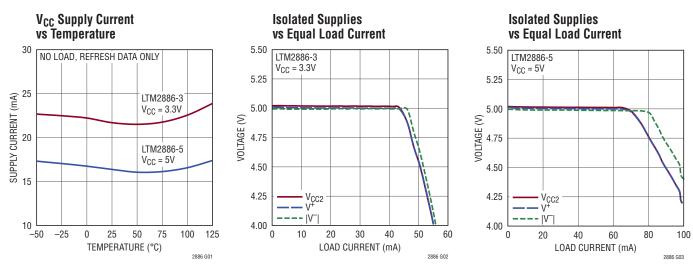
Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

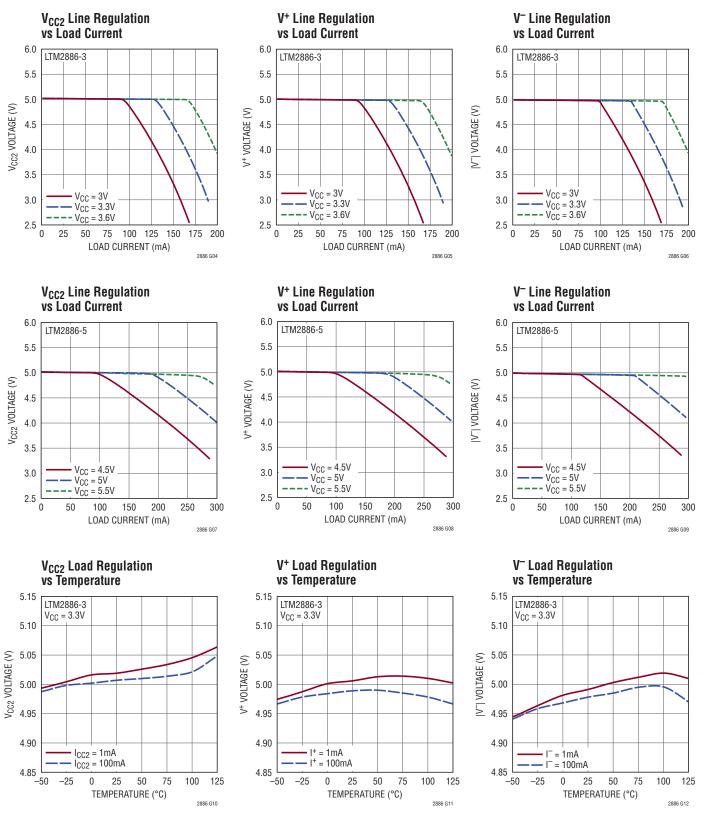
Note 2: Guaranteed by design and not subject to production test.

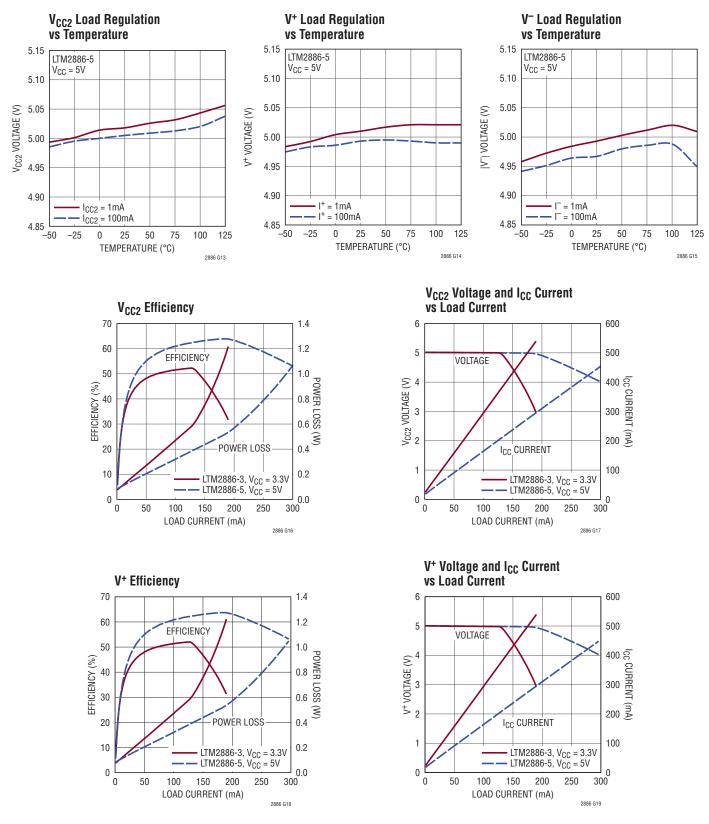
Note 3: Maximum Data rate is guaranteed by other measured parameters and is not tested directly.

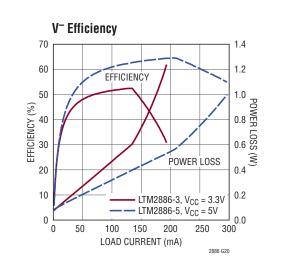
Note 4: This Module includes overtemperature protection that is intended to protect the device during momentary overload conditions. Junction temperature will exceed 125°C when overtemperature protection is active. Continuous operation above specified maximum operating junction temperature may result in device degradation or failure.

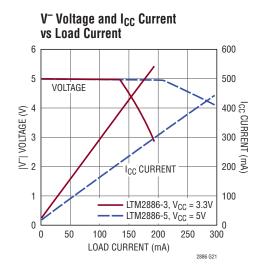
Note 5: Device considered a 2-terminal device. Pin group A1 through B8 shorted together and pin group K1 through L8 shorted together. **Note 6:** The rated dielectric insulation voltage should not be interpreted as a continuous voltage rating.



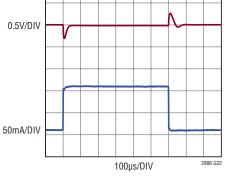




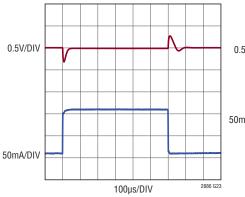




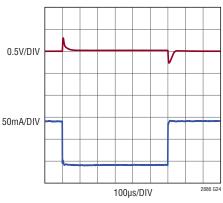
V_{CC2} Transient Response 100mA Load Step



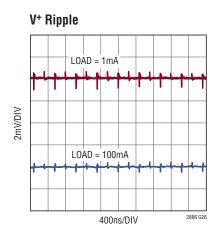
V⁺ Transient Response 100mA Load Step



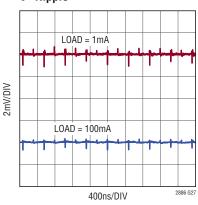
V⁻ Transient Response 100mA Load Step

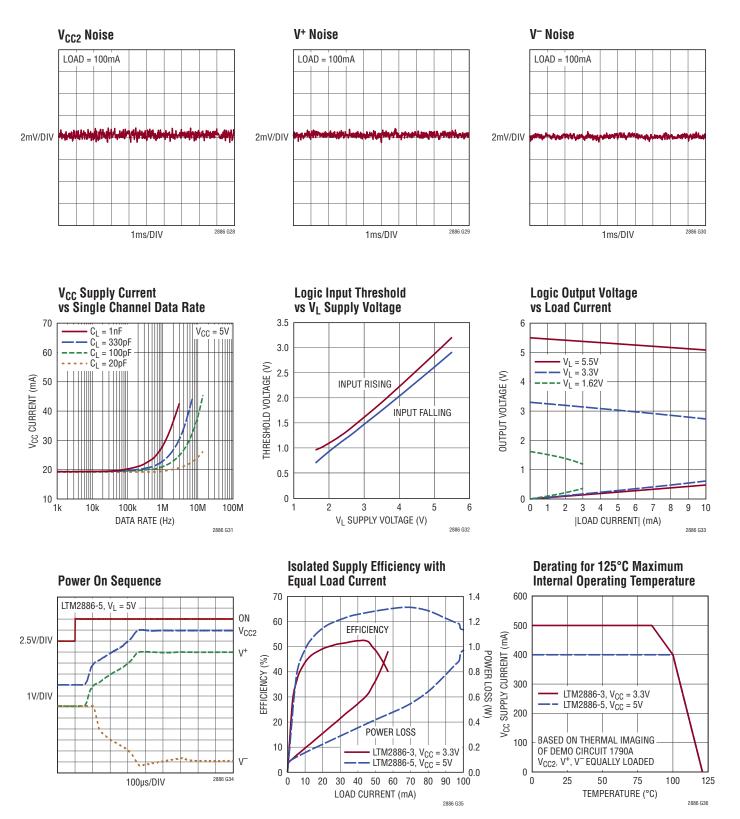


V_{CC2} Ripple LOAD = 1mA 2mV/DIV LOAD = 100mA 2886 G25 400ns/DIV









PIN FUNCTIONS (LTM2886-I)

Logic Side

D02 (A1): Digital Output, Referenced to V_L and GND. Logic output connected to I2 through isolation barrier. Under the condition of an isolation communication failure this output is in a high impedance state.

DNC (A2): Do Not Connect. Pin connected internally.

SCL (A3): Serial I²C Clock Input, Referenced to V_L and GND. Logic input connected to isolated side SCL2 pin through isolation barrier. Clock is unidirectional from logic to isolated side. Do not float.

SDA (A4): Serial I²C Data Pin, Referenced to V_L and GND. Bidirectional logic pin connected to isolated side SDA2 pin through isolation barrier. Under the condition of an isolation communication failure this pin is in a high impedance state. Do not float.

DI1 (A5): Digital Input, Referenced to V_L and GND. Logic input connected to O1 through isolation barrier. The logic state on DI1 translates to the same logic state on O1. Do not float.

GND (A6, B2 to B6): Circuit Ground.

ON (A7): Enable, Referenced to V_L and GND. Enables power and data communication through the isolation barrier. If ON is high the part is enabled and power and communications are functional to the isolated side. If ON is low the logic side is held in reset, all digital outputs are in a high impedance state, and the isolated side is unpowered. Do not float.

 V_L (A8): Logic Supply. Interface supply voltage for pins D11, SCL, SDA, D01, D02, and ON. Operating voltage is 1.62V to 5.5V. Internally bypassed with 1µF.

D01 (B1): Digital Output, Referenced to V_L and GND. Logic output connected to 11 through isolation barrier. Under the condition of an isolation communication failure this output is in a high impedance state.

 V_{CC} (**B7 to B8**): Supply Voltage. Operating voltage is 3V to 3.6V for LTM2886-3 and 4.5V to 5.5V for LTM2886-5. Internally bypassed with 2.2µF.

Isolated Side

I2 (L1): Digital Input, Referenced to V_{CC2} and GND2. Logic input connected to DO2 through isolation barrier.

The logic state on I2 translates to the same logic state on DO2. Do not float.

DNC (L2): Do Not Connect. Pin connected internally.

SCL2 (L3): Serial I²C Clock Output, Referenced to V_{CC2} and GND2. Logic output connected to logic side SCL pin through isolation barrier. Clock is unidirectional from logic to isolated side. SCL2 has a push-pull output stage, do not connect an external pull-up device. Under the condition of an isolation communication failure this output defaults to a high state.

SDA2 (L4): Serial I²C Data Pin, Referenced to V_{CC2} and GND2. Bidirectional logic pin connected to logic side SDA pin through isolation barrier. Output is biased high by a 1.8mA current source. Do not connect an external pullup device to SDA2. Under the condition of an isolation communication failure this output defaults to a high state.

01 (L5): Digital Output, Referenced to V_{CC2} and GND2. Logic output connected to DI1 through isolation barrier. Under the condition of an isolation communication failure 01 defaults to a high state.

 V_{CC2} (L6): 3V to 5.5V Adjustable Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to 5V with no external components. Internally bypassed with 2.2µF.

V⁻ (L7): -5V Nominal Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to -5V with no external components. Internally bypassed with 2.2µF.

V⁺ (L8): 5V Nominal Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to 5V with no external components. Internally bypassed with 2.2µF.

I1 (K1): Digital Input, Referenced to V_{CC2} and GND2. Logic input connected to DO1 through isolation barrier. The logic state on I1 translates to the same logic state on DO1. Do not float.

GND2 (K2 to K5, K7, K8): Isolated Ground.

AV_{CC2} (K6): 5V Nominal Isolated Supply Voltage Adjust. The adjust pin voltage is 1.22V referenced to GND2. See Applications Information section for details.

PIN FUNCTIONS (LTM2886-S)

Logic Side

SDO (A1): Serial SPI Digital Output, Referenced to V_L and GND. Logic output connected to isolated side SDO2 pin through isolation barrier. Under the condition of an isolation communication failure this output is in a high impedance state.

D02 (A2): Digital Output, Referenced to V_L and GND. Logic output connected to I2 through isolation barrier. Under the condition of an isolation communication failure this output is in a high impedance state.

SCK (A3): Serial SPI Clock Input, Referenced to V_L and GND. Logic input connected to isolated side SCK2 pin through isolation barrier. Do not float.

SDI (A4): Serial SPI Data Input, Referenced to V_L and GND. Logic input connected to isolated side SDI2 pin through isolation barrier. Do not float.

 $\overline{\text{CS}}$ (A5): Serial SPI Chip Select, Referenced to V_L and GND. Logic input connected to isolated side $\overline{\text{CS2}}$ pin through isolation barrier. Do not float.

SDOE (A6): Serial SPI Data Output Enable, Referenced to V_L and GND. A logic high on SDOE places the logic side SDO pin in a high impedance state, a logic low enables the output. Do not float.

ON (A7): Enable, Referenced to V_L and GND. Enables power and data communication through the isolation barrier. If ON is high the part is enabled and power and communications are functional to the isolated side. If ON is low the logic side is held in reset, all digital outputs are in a high impedance state, and the isolated side is unpowered. Do not float.

 V_L (A8): Logic Supply. Interface supply voltage for pins SDI, SCK, SDO, SDOE, DO1, DO2, \overline{CS} , and ON. Operating voltage is 1.62V to 5.5V. Internally bypassed with 1µF.

D01 (B1): Digital Output, Referenced to V_L and GND. Logic output connected to 11 through isolation barrier. Under the condition of an isolation communication failure this output is in a high impedance state.

GND (B2 to B6): Circuit Ground.

 V_{CC} (B7 to B8): Supply Voltage. Operating voltage is 3V to 3.6V for LTM2886-3 and 4.5V to 5.5V for LTM2886-5. Internally bypassed with 2.2µF.

Isolated Side

SD02 (L1): Serial SPI Digital Input, Referenced to V_{CC2} and GND2. Logic input connected to logic side SDO pin through isolation barrier. Do not float.

12 (L2): Digital Input, Referenced to V_{CC2} and GND2. Logic input connected to DO2 through isolation barrier. The logic state on I2 translates to the same logic state on DO2. Do not float.

SCK2 (L3): Serial SPI Clock Output, Referenced to V_{CC2} and GND2. Logic output connected to logic side SCK pin through isolation barrier. Under the condition of an isolation communication failure this output defaults to a low state.

SDI2 (L4): Serial SPI Data Output, Referenced to V_{CC2} and GND2. Logic output connected to logic side SDI pin through isolation barrier. Under the condition of an isolation communication failure this output defaults to a low state.

CS2 (L5): Serial SPI Chip Select, Referenced to V_{CC2} and GND2. Logic output connected to logic side \overline{CS} pin through isolation barrier. Under the condition of an isolation communication failure this output defaults to a high state.

 V_{CC2} (L6): 3V to 5.5V Adjustable Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to 5V with no external components. Internally bypassed with 2.2µF.

V⁻ (L7): -5V Nominal Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to -5V with no external components. Internally bypassed with 2.2µF.

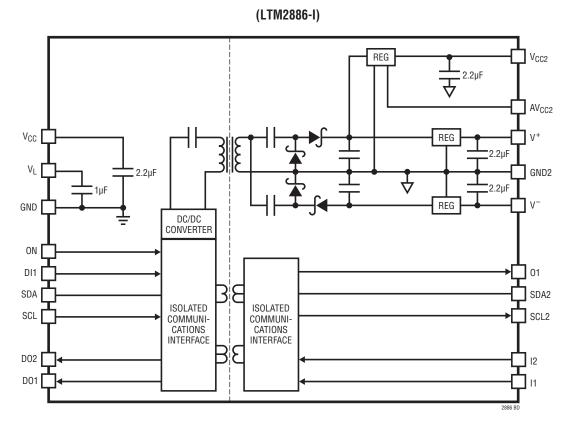
V⁺ (L8): 5V Nominal Isolated Supply Voltage. Internally generated from V_{CC} by an isolated DC/DC converter and regulated to 5V with no external components. Internally bypassed with 2.2µF.

I1 (K1): Digital Input, Referenced to V_{CC2} and GND2. Logic input connected to DO1 through isolation barrier. The logic state on I1 translates to the same logic state on DO1. Do not float.

GND2 (K2 to K5, K7, K8): Isolated Ground.

AV_{CC2} (K6): 5V Nominal Isolated Supply Voltage Adjust. The adjust pin voltage is 1.22V Referenced to GND2. See Applications Information section for details.

BLOCK DIAGRAMS

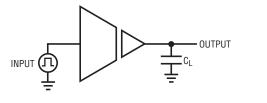


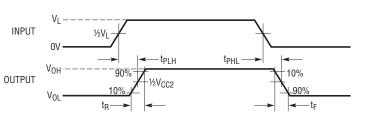
(LTM2886-S) REG V_{CC2} 2.2µF ∀ AV_{CC2} ► $\rm V_{\rm CC}$ REG V+ E 3 2.2µF V_{L} 2.2µF GND2 2.2µF 1µF DC/DC CONVERTER REG V⁻ GND -ON SDOE $\overline{\text{CS}}$ $\overline{CS2}$ 38 SDI SDI2 ISOLATED COMMUNI-CATIONS INTERFACE ISOLATED COMMUNI-SCK SCK2 CATIONS INTERFACE D02 12 Bie SDO SD02 D01 11 2886 BDa

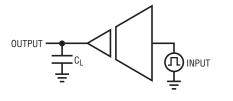
5

LTM2886

TEST CIRCUITS







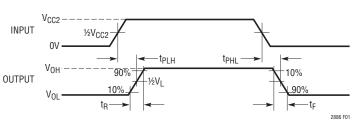
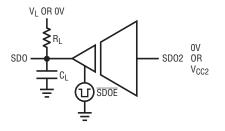


Figure 1. Logic Timing Measurements



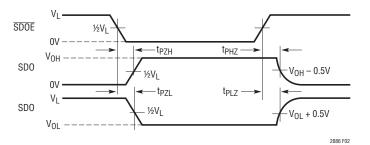
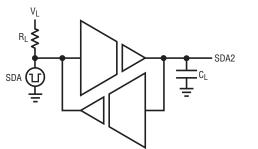
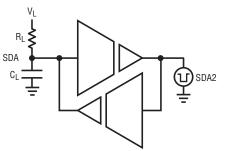
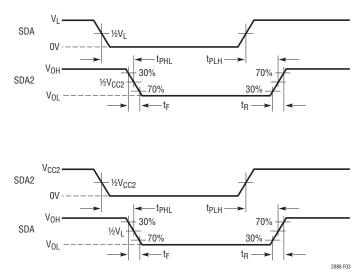


Figure 2. Logic Enable/Disable Time









Overview

The LTM2886 digital μ Module isolator provides a galvanically-isolated robust logic interface, powered by an integrated, regulated DC/DC converter, complete with decoupling capacitors. The LTM2886 is ideal for use in networks where grounds can take on different voltages. Isolation in the LTM2886 blocks high voltage differences, eliminates ground loops and is extremely tolerant of common mode transients between ground planes. Error-free operation is maintained through common mode events greater than 30kV/ μ s providing excellent noise isolation.

Isolator µModule Technology

The LTM2886 utilizes isolator μ Module technology to translate signals and power across an isolation barrier. Signals on either side of the barrier are encoded into pulses and translated across the isolation boundary using coreless transformers formed in the μ Module substrate. This system, complete with data refresh, error checking, safe shutdown on fail, and extremely high common mode immunity, provides a robust solution for bidirectional signal isolation. The μ Module technology provides the means to combine the isolated DC/DC converter in one small package.

DC/DC Converter

The LTM2886 contains a fully integrated DC/DC converter, including the transformer, so that no external components are necessary. The logic side contains a full-bridge driver, running at 1.6MHz, and is AC-coupled to a single transformer primary. A series DC blocking capacitor prevents transformer saturation due to driver duty cycle imbalance. The transformer scales the primary voltage, and is rectified by a voltage quadrupler. This topology eliminates transformer saturation caused by secondary imbalances.

The quadrupler is grounded in the middle producing symmetrical positive and negative voltage rails. The positive rail is post regulated with two low dropout regulators (LDOs) producing V_{CC2} and V⁺, the negative rail also has an LDO producing V⁻.

Each voltage rail is capable of producing 100mA of output current, total output power capability is approximately 1W. All voltage rails are bypassed with 2.2μ F ceramic capacitors.

V_L Logic Supply

A separate logic supply pin V_L allows the LTM2886 to interface with any logic signal from 1.62V to 5.5V as shown in Figure 4. Simply connect the desired logic supply to V_L.

There is no interdependency between V_{CC} and V_L; they may simultaneously operate at any voltage within their specified operating ranges and sequence in any order. V_L is bypassed internally by a 1 μ F capacitor.

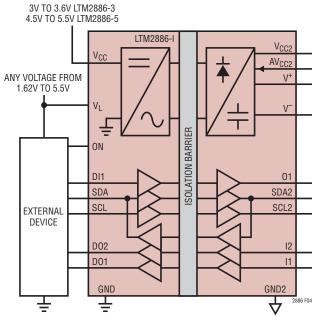


Figure 4. $V_{\mbox{CC}}$ and $V_{\mbox{L}}$ Are Independent

Hot-Plugging Safely

Caution must be exercised in applications where power is plugged into the LTM2886's power supplies, V_{CC} or V_L , due to the integrated ceramic decoupling capacitors. The parasitic cable inductance along with the high Q characteristics of ceramic capacitors can cause substantial ringing which could exceed the maximum voltage ratings and damage the LTM2886. Refer to Linear Technology Application Note 88, entitled Ceramic Input Capacitors Can Cause Overvoltage Transients for a detailed discussion and mitigation of this phenomenon.

Isolated Supply Adjustable Operation

The V_{CC2} isolated power rail is nominally 5V, but may be overdriven by adding two external resistors. The unadjusted output voltage represents the maximum for guaranteed performance. Figure 5 illustrates configuration for V_{CC2} = 3.3V, V⁺ and V⁻ are fixed at 5V and -5V respectively.

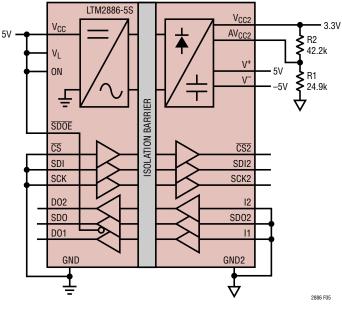


Figure 5. Adjustable Voltage Rails

The output adjustment range for V_{CC2} is 3V to 5.5V. V_{CC2} output voltage is calculated by:

 $V_{CC2} = 1.22V(1 + R2/R1)$

The value of R1 should be no greater than 24.9k to minimize errors in the output voltage caused by the AV_{CC2} pin bias current.

Operation at low output voltages may result in thermal shutdown due to low dropout regulator power dissipation.

Channel Timing Uncertainty

Multiple channels are supported across the isolation boundary by encoding and decoding of the inputs and outputs. Up to three signals in each direction are assembled as a packet and transferred across the isolation barrier. The time required to transfer all 3 bits is 100ns maximum, and sets the limit for how often a signal can change on the opposite side of the barrier. Encoding transmission is independent for each data direction. The technique used assigns SCK or SCL on the logic side, and SDO2 or I2 on the isolated side, the highest priority such that there is no jitter on the associated output channels, only delay. This preemptive scheme will produce a certain amount of uncertainty on the other isolation channels. The resulting pulse width uncertainty on these low priority channels is typically ±6ns, but may vary up to ±50ns if the low priority channels are not encoded within the same high priority serial packet.

Serial Peripheral Interface (SPI) Bus

The LTM2886-S provides a SPI compatible isolated interface. The maximum data rate is a function of the inherent channel propagation delays, channel to channel pulse width uncertainty, and data direction requirements. Channel timing is detailed in Figures 6 through 9 and Tables 2 and 3. The SPI protocol supports four unique timing configurations defined by the clock polarity (CPOL) and clock phase (CPHA) summarized in Table 1.

Table 1. SPI Mode

CPOL	CPHA	DATA TO (CLOCK	DATA TO (CLOCK) RELATIONSHIP		
0	0	Sample (Rising)	Set-Up (Falling)		
0	1	Set-Up (Rising)	Sample (Falling)		
1	0	Sample (Falling)	Set-Up (Rising)		
1	1	Set-Up (Falling)	Sample (Rising)		

The maximum data rate for bidirectional communication is 4MHz, based on a synchronous system, as detailed in the timing waveforms. Slightly higher data rates may be achieved by skewing the clock duty cycle and minimizing the SDO to SCK set-up time, however the clock rate is still dominated by the system propagation delays. A discussion of the critical timing paths relative to Figures 6 and 7 follows.

- CS to SCK (master sample SD0, 1st SD0 valid)
 - $t_0 \rightarrow t_1$ ~50ns, $\overline{\text{CS}}$ to $\overline{\text{CS2}}$ propagation delay
 - $\begin{array}{ll} t_1 \rightarrow t_{1+} & \mbox{Isolated slave device propagation} \\ (\mbox{response time}), \mbox{asserts SD02} \end{array}$
 - $t_1 \mathop{\rightarrow} t_3 \quad \ \ \approx 50 \text{ns}, \, \text{SDO2 to SDO propagation delay}$
 - $t_3 \rightarrow t_5$ Set-up time for master SDO to SCK
- SDI to SCK (master data write to slave)
 - $t_2 \mathop{\rightarrow} t_4 \quad \ \approx 50 \text{ns}, \, \text{SDI to SDI2 propagation delay}$
 - $t_5 \mathop{\rightarrow} t_6 \quad \ \ \approx 50 \text{ns}, \, \text{SCK to SCK2 propagation delay}$
 - $\begin{array}{ll} t_2 \rightarrow t_5 & \geq 50 \text{ns, SDI to SCK, separate packet} \\ & \text{non-zero set-up time} \end{array}$
 - $\begin{array}{ll} t_4 \rightarrow t_6 & \geq 50 \text{ns, SDI2 to SCK2, separate packet} \\ & \text{non-zero set-up time} \end{array}$
- SDO to SCK (master sample SDO, subsequent SDO valid)
 - t_8 set-up data transition SDI and SCK
 - $t_8 \,{\rightarrow}\, t_{10} \quad \approx 50 \text{ns}, \, \text{SDI} \text{ to SDI2} \text{ and SCK to SCK2} \\ propagation \ delay$

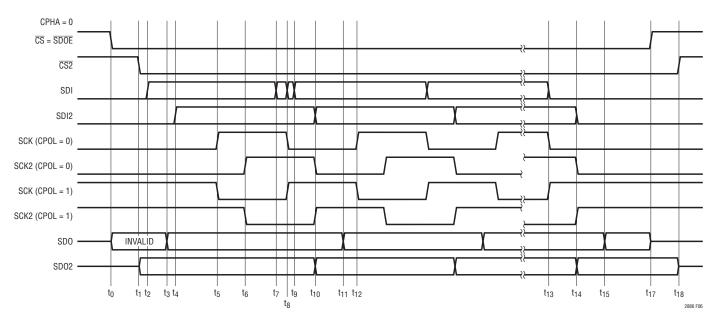
- t_{10} SD02 data transition in response to SCK2
- $t_{10} \mathop{\rightarrow} t_{11} ~\approx 50 \text{ns}, \, \text{SDO2} \text{ to SDO propagation delay}$
- $t_{11} \mathop{\rightarrow} t_{12}~$ Set-up time for master SDO to SCK

Maximum data rate for single direction communication, master to slave, is 8MHz, limited by the systems encoding/decoding scheme or propagation delay. Timing details for both variations of clock phase are shown in Figures 8 and 9 and Table 3.

Additional requirements to insure maximum data rate are:

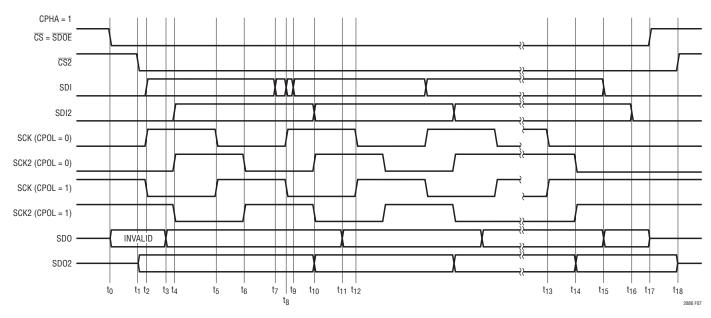
- CS is transmitted prior to (asynchronous) or within the same (synchronous) data packet as SDI
- SDI and SCK set-up data transition occur within the same data packet. Referencing Figure 6, SDI can precede SCK by up to 13ns $(t_7 \rightarrow t_8)$ or lag SCK by 3ns $(t_8 \rightarrow t_9)$ and not violate this requirement. Similarly in Figure 8, SDI can precede SCK by up to 13ns $(t_4 \rightarrow t_5)$ or lag SCK by 3ns $(t_5 \rightarrow t_6)$.

2886fb

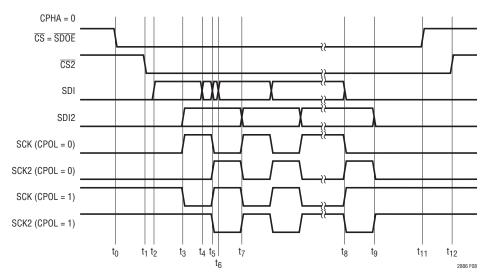














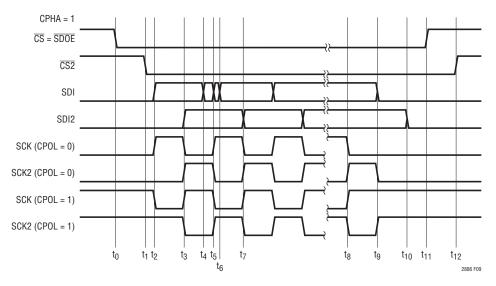




Table 2. Bidirectional SPI Timing Event Description

TIME	CPHA	EVENT DESCRIPTION
to	0, 1	Asynchronous chip select, may be synchronous to SDI but may not lag by more than 3ns. Logic side slave data output enabled, initial data is not equivalent to slave device data output
t ₀ to t _{1,} t ₁₇ to t ₁₈	0, 1	Propagation delay chip select, logic to isolated side, 50ns typical
t ₁	0, 1	Slave device chip select output data enable
t ₂	0	Start of data transmission, data set-up
	1	Start of transmission, data and clock set-up. Data transition must be within –13ns to 3ns of clock edge
t ₁ to t ₃	0, 1	Propagation delay of slave data, isolated to logic side, 50ns typical
t ₃	0, 1	Slave data output valid, logic side
t ₂ to t ₄	0	Propagation delay of data, logic side to isolated side
	1	Propagation delay of data and clock, logic side to isolated side
t ₅	0, 1	Logic side data sample time, half clock period delay from data set-up transition
t ₅ to t ₆	0, 1	Propagation delay of clock, logic to isolated side
t ₆	0, 1	Isolated side data sample time
t ₈	0, 1	Synchronous data and clock transition, logic side
t ₇ to t ₈	0, 1	Data to clock delay, must be \leq 13ns
t ₈ to t ₉	0, 1	Clock to data delay, must be ≤3ns
t ₈ to t ₁₀	0, 1	Propagation delay clock and data, logic to isolated side
t ₁₀ , t ₁₄	0, 1	Slave device data transition
t ₁₀ to t _{11,} t ₁₄ to t ₁₅	0, 1	Propagation delay slave data, isolated to logic side
t ₁₁ to t ₁₂	0, 1	Slave data output to sample clock set-up time
t ₁₃	0	Last data and clock transition logic side
	1	Last sample clock transition logic side
t ₁₃ to t ₁₄	0	Propagation delay data and clock, logic to isolated side
	1	Propagation delay clock, logic to isolated side
t ₁₅	0	Last slave data output transition logic side
	1	Last slave data output and data transition, logic side
t ₁₅ to t ₁₆	1	Propagation delay data, logic to isolated side
t ₁₇	0, 1	Asynchronous chip select transition, end of transmission. Disable slave data output logic side
t ₁₈	0, 1	Chip select transition isolated side, slave data output disabled

Inter-IC Communication (I²C) Bus

The LTM2886-I provides an I²C compatible isolated interface. Clock (SCL) is unidirectional, supporting master mode only, and data (SDA) is bidirectional. The maximum data rate is 400kHz which supports fast-mode I²C. Timing is detailed in Figure 10. The data rate is limited by the slave acknowledge setup time ($t_{SU;ACK}$), consisting of the I²C standard minimum setup time ($t_{SU;DAT}$) of 100ns, maximum clock propagation delay of 225ns, glitch filter and isolated data delay of 500ns maximum, and the combined isolated and logic data fall time of 300ns at maximum bus loading. The total setup time reduces the l²C data hold time ($t_{HD;DAT}$) to a maximum of 175ns, guaranteeing sufficient data setup time ($t_{SU;ACK}$).

The isolated side bidirectional serial data pin, SDA2, simplified schematic is shown in Figure 11. An internal 1.8mA current source provides a pull-up for SDA2. Do not connect any other pull-up device to SDA2. This current source is sufficient to satisfy the system requirements for bus capacitances greater than 200pF in FAST mode and greater than 400pF in STANDARD mode.

TIME	СРНА	EVENT DESCRIPTION
t ₀	0, 1	Asynchronous chip select, may be synchronous to SDI but may not lag by more than 3ns
t ₀ to t ₁	0, 1	Propagation delay chip select, logic to isolated side
t ₂	0	Start of data transmission, data set-up
	1	Start of transmission, data and clock set-up. Data transition must be within –13ns to 3ns of clock edge
t ₂ to t ₃	0	Propagation delay of data, logic side to isolated side
	1	Propagation delay of data and clock, logic side to isolated side
t ₃	0, 1	Logic side data sample time, half clock period delay from data set-up transition
t ₃ to t ₅	0, 1	Clock propagation delay, clock and data transition
t ₄ to t ₅	0, 1	Data to clock delay, must be ≤13ns
t ₅ to t ₆	0, 1	Clock to data delay, must be ≤3ns
t5 t0 t7	0, 1	Data and clock propagation delay
t ₈	0	Last clock and data transition
	1	Last clock transition
t ₈ to t ₉	0	Clock and data propagation delay
	1	Clock propagation delay
t ₉ to t ₁₀	1	Data propagation delay
t ₁₁	0, 1	Asynchronous chip select transition, end of transmission
t ₁₂	0, 1	Chip select transition isolated side

Table 3. Unidirectional SPI Timing Event Description

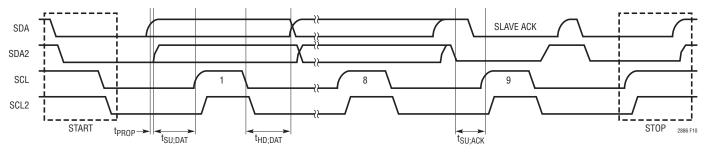


Figure 10. I²C Timing Diagram

Additional proprietary circuitry monitors the slew rate on the SDA and SDA2 signals to manage directional control across the isolation barrier. Slew rates on both pins must be greater than $1V/\mu$ s for proper operation.

The logic side bidirectional serial data pin, SDA, requires a pull-up resistor or current source connected to V_L. Follow the requirements in Figures 12 and 13 for the appropriate pull-up resistor on SDA that satisfies the desired rise time specifications and V_{OL} maximum limits for FAST and STANDARD modes. The resistance curves represent the maximum resistance boundary; any value may be used to the left of the appropriate curve.

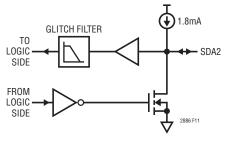
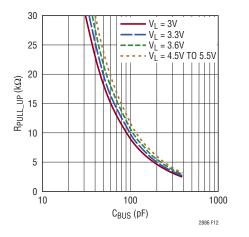


Figure 11. Isolated SDA2 Pin Schematic





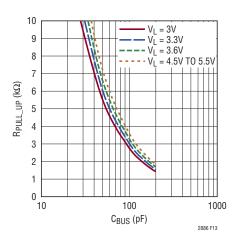


Figure 13. Maximum Fast Speed Pull-Up Resistance on SDA

The isolated side clock pin, SCL2, has a weak push-pull output driver; do not connect an external pull-up device. SCL2 is compatible with I²C devices without clock stretching. On lightly loaded connections, a 100pF capacitor from SCL2 to GND2 or RC lowpass filter (R = 500Ω , C = 100pF) can be used to increase the rise and fall times and minimize noise.

Some consideration must be given to signal coupling between SCL2 and SDA2. Separate these signals on a printed circuit board or route with ground between.

If these signals are wired off board, twist SCL2 with V_{CC2} and/or GND2 and SDA2 with GND2 and/or V_{CC2}, do not twist SCL2 and SDA2 together. If coupling between SCL2 and SDA2 is unavoidable, place the aforementioned RC filter at the SCL2 pin to reduce noise injection onto SDA2.

Low Noise Applications

For precision analog applications the V⁺ and V⁻ power rails may be filtered to improve the noise performance. Figure 14 shows the recommended component values to reduce noise at high frequencies. The selected inductor should be chosen such that the parasitic capacitance is low enough to keep the self resonant frequency greater than 10MHz. The plots of Figures 15 and 16 show the high frequency noise improvement for the V⁺ rail, the improvement on the V⁻ rail will be nearly equivalent.

Some applications may require the noise performance be improved in the 100Hz to 10kHz region. An additional LC filter stage may be added between the LTM2886 and the high frequency filter to lower the noise corner frequency. Using an inductance of 330μ H and capacitance of 680μ F reduces the noise corner to approximately 340Hz. The RMS noise at a bandwidth of 340Hz is approximately 22μ V.

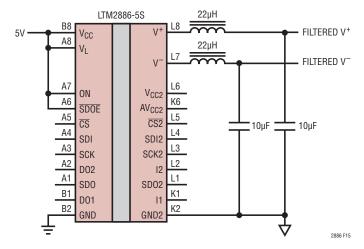


Figure 14. Filtered Voltage Rails for Low Noise Applications

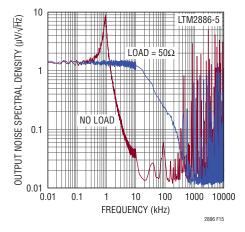


Figure 15. V⁺ Output Noise Spectral Density Without Filter

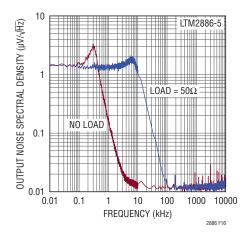


Figure 16. V⁺ Output Noise Spectral Density With Filter

RF, Magnetic Field Immunity

The isolator μ Module technology used within the LTM2886 has been independently evaluated, and successfully passed the RF and magnetic field immunity testing requirements per European Standard EN 55024, in accordance with the following test standards:

EN 61000-4-3	Radiated, Radio-Frequency, Electromagnetic Field Immunity
EN 61000-4-8	Power Frequency Magnetic Field Immunity

EN 61000-4-9 Pulsed Magnetic Field Immunity

Tests were performed using an unshielded test card designed per the data sheet PCB layout recommendations. Specific limits per test are detailed in Table 5.

Table 4. EMC Immunity Tests

,				
TEST	FREQUENCY	FIELD STRENGTH		
EN 61000-4-3 Annex D	80MHz to 1GHz	10V/m		
	1.4MHz to 2GHz	3V/m		
	2GHz to 2.7GHz	1V/m		
EN 61000-4-8 Level 4	50Hz and 60Hz	30A/m		
EN 61000-4-8 Level 5	60Hz	100A/m*		
EN 61000-4-9 Level 5	Pulse	1000A/m		
* a s a IEO as stils s d	-	÷		

*non IEC method

PCB Layout

The high integration of the LTM2886 makes PCB layout very simple. However, to optimize its electrical isolation characteristics, EMI, and thermal performance, some layout considerations are necessary.

- Under heavily loaded conditions V_{CC} and GND current can exceed 300mA. Sufficient copper must be used on the PCB to insure resistive losses do not cause the supply voltage to drop below the minimum allowed level. Similarly, the V_{CC2} and GND2 conductors must be sized to support any external load current. These heavy copper traces will also help to reduce thermal stress and improve the thermal conductivity.
- Input and output supply decoupling is not required, since these components are integrated within the package. An additional bulk capacitor with a value of 6.8µF to 22µF is recommended. The high ESR of this capacitor reduces board resonances and minimizes voltage spikes caused by hot plugging of the supply voltage. For EMI sensitive applications, an additional low ESL ceramic capacitor of 1µF to 4.7µF, placed as close to the power and ground terminals as possible, is recommended. Alternatively, a number of smaller value parallel capacitors may be used to reduce ESL and achieve the same net capacitance.
- Do not place copper on the PCB between the inner columns of pads. This area must remain open to withstand the rated isolation voltage.
- The use of solid ground planes for GND and GND2 is recommended for non-EMI critical applications to optimize signal fidelity, thermal performance, and to minimize RF emissions due to uncoupled PCB trace

conduction. The drawback of using ground planes, where EMI is of concern, is the creation of a dipole antenna structure which can radiate differential voltages formed between GND and GND2. If ground planes are used it is recommended to minimize their area, and use contiguous planes as any openings or splits can exacerbate RF emissions.

- For large ground planes a small capacitance (\leq 330pF) • from GND to GND2, either discrete or embedded within the substrate, provides a low impedance current return path for the module parasitic capacitance, minimizing any high frequency differential voltages and substantially reducing radiated emissions. Discrete capacitance will not be as effective due to parasitic ESL. In addition, voltage rating, leakage, and clearance must be considered for component selection. Embedding the capacitance within the PCB substrate provides a near ideal capacitor and eliminates component selection issues; however, the PCB must be four layers. Care must be exercised in applying either technique to ensure the voltage rating of the barrier is not compromised.
- In applications without an embedded PCB substrate capacitance a slot may be added between the logic side and isolated side device pins. The slot extends the creepage path between terminals on the PCB side, and may reduce leakage caused by PCB contamination. The slot should be placed in the middle of the device and extend beyond the package perimeter.

The PCB layout in Figures 17 and 18 shows the low EMI demo board for the LTM2886. The demo board uses a combination of EMI mitigation techniques, including both embedded PCB bridge capacitance and discrete GND to GND2 capacitors. Two safety rated type Y2 capacitors are used in series, manufactured by MuRata, part number GA342QR7GF471KW01L. The embedded capacitor effectively suppresses emissions above 400MHz, whereas the discrete capacitors are more effective below 400MHz.

EMI performance is shown in Figure 19, measured using a Gigahertz Transverse Electromagnetic (GTEM) cell and method detailed in IEC 61000-4-20, Testing and Measurement Techniques – Emission and Immunity Testing in Transverse Electromagnetic Waveguides.

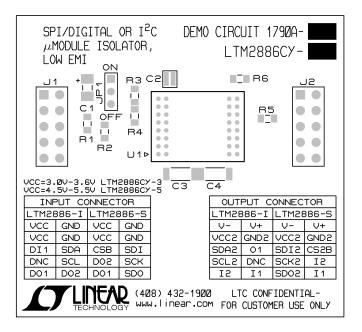
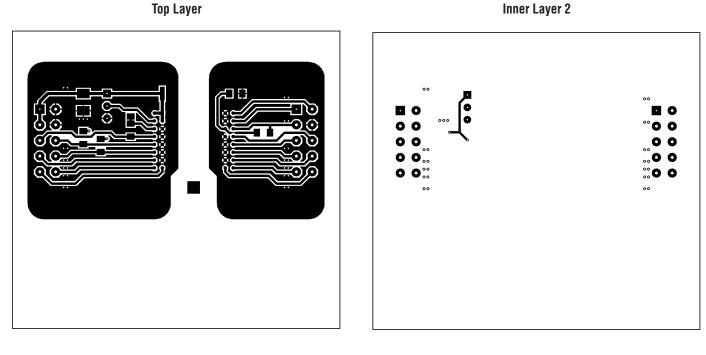


Figure 17. LTM2886 Low EMI Demo Board Layout

Bottom Layer

APPLICATIONS INFORMATION

Top Layer



Inner Layer 1

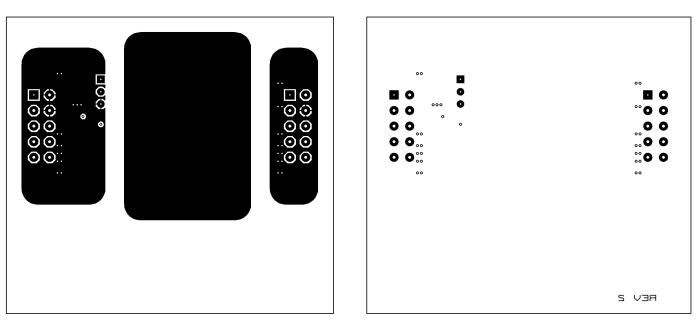


Figure 18. LTM2886 Low EMI Demo Board Layout (DC1790A)

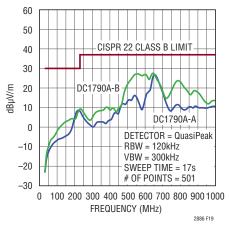


Figure 19. LTM2886 Low EMI Demo Board Emissions

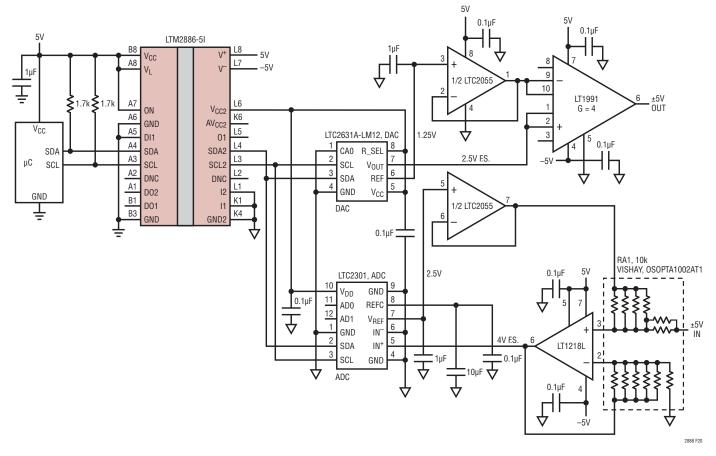


Figure 20. Isolated I²C 12-Bit, ±5V Analog Input and Output

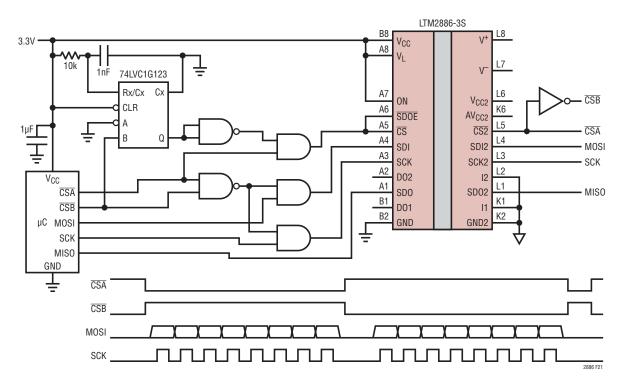


Figure 21. Isolated SPI Device Expansion

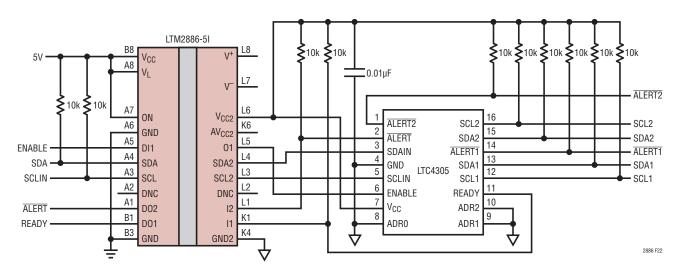


Figure 22. Isolated I²C Buffer with Dual Outputs

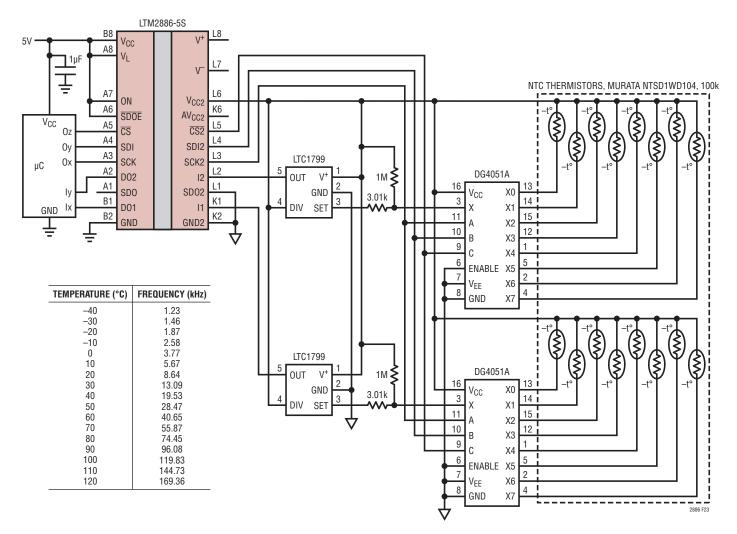


Figure 23. 16-Channel Isolated Temperature to Frequency Converter

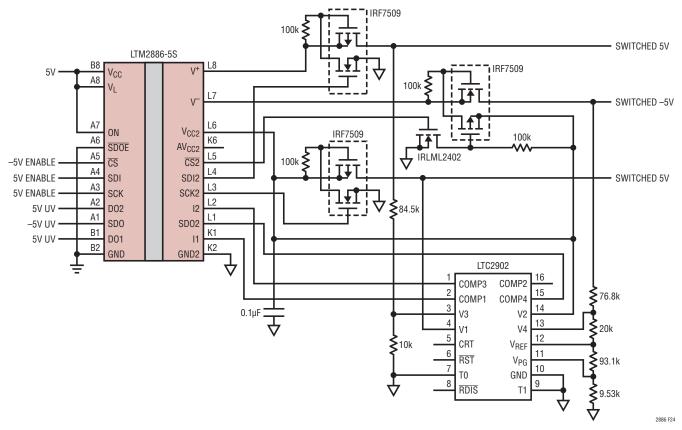


Figure 24. Digitally Switched Triple Power Supply with Undervoltage Monitor

2886fb

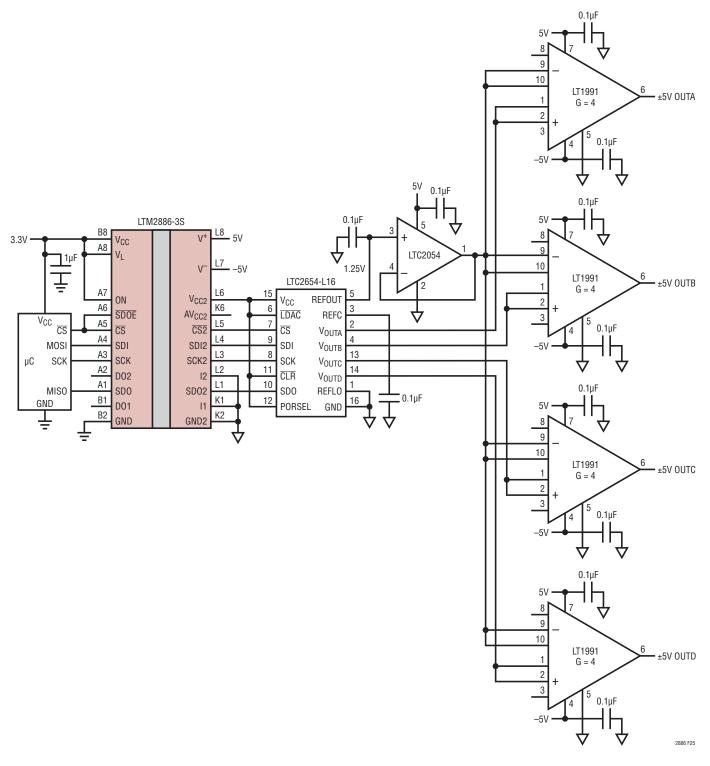


Figure 25. Quad 16-Bit ±5V Output Range DAC

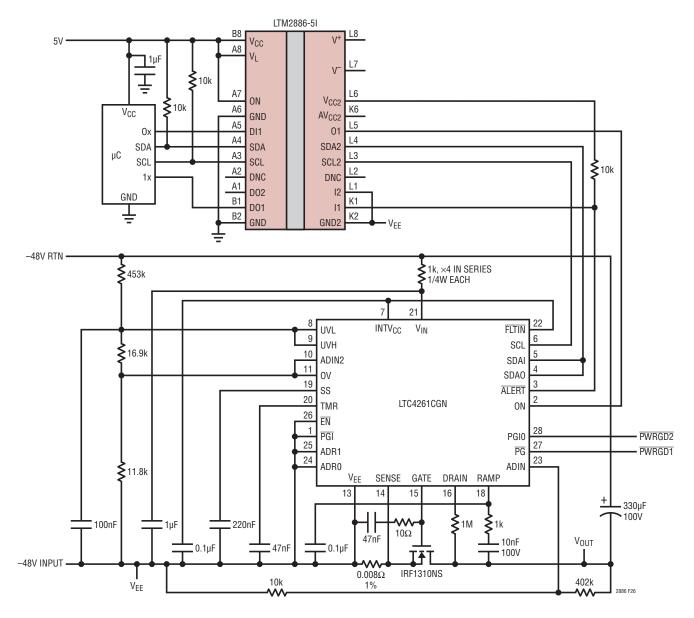


Figure 26. –48V, 200W Hot Swap Controller with Isolated I²C Interface

2886fb

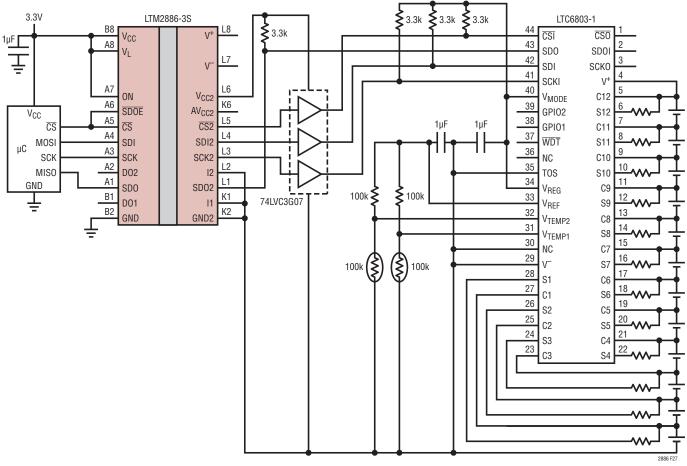
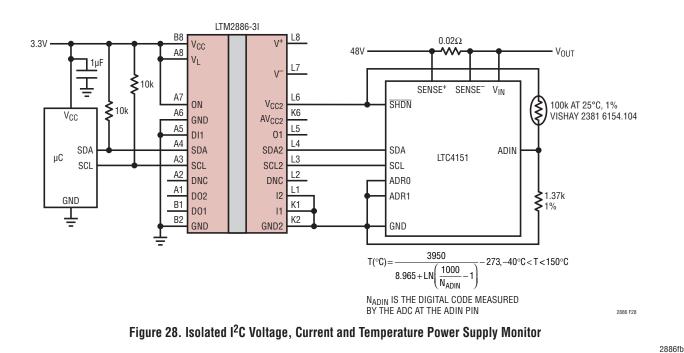


Figure 27. 12-Cell Battery Stack Monitor with Isolated SPI Interface and Low Power Shutdown



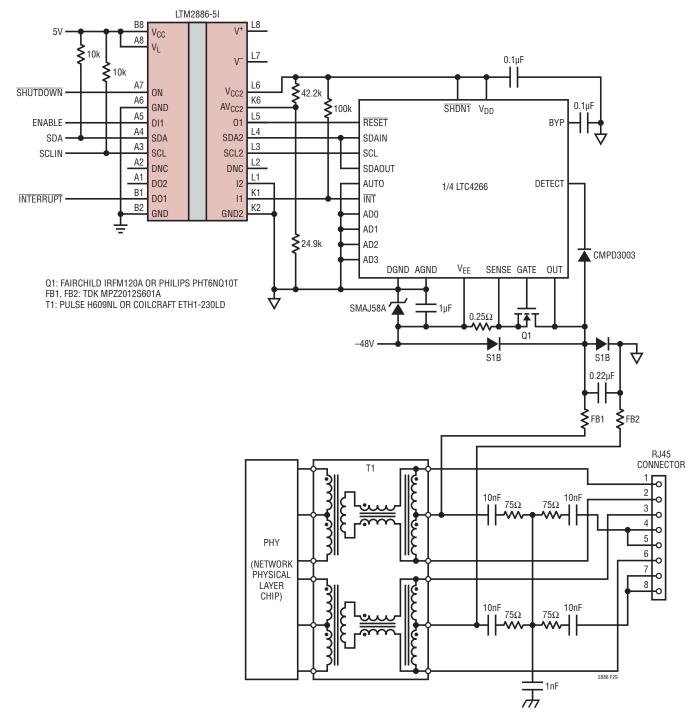
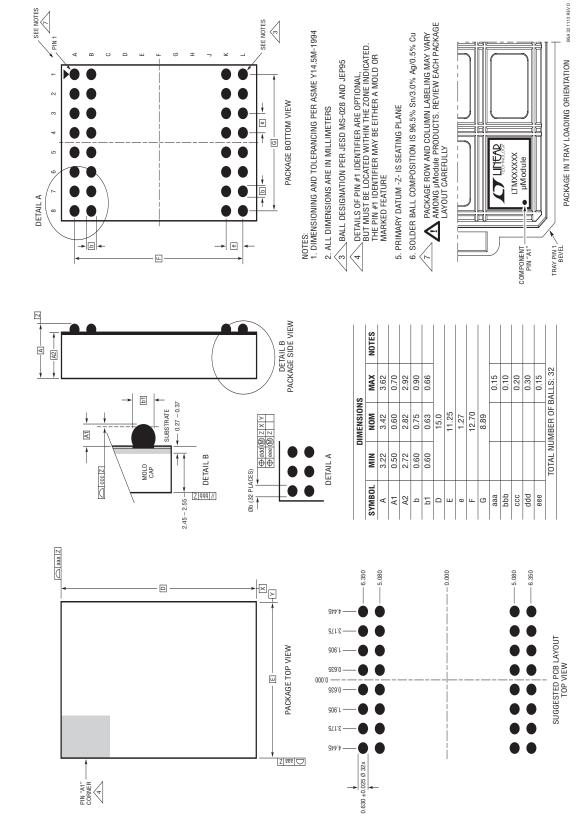


Figure 29. One Complete Isolated Powered Ethernet Port

2886fb

PACKAGE DESCRIPTION

Please refer to http://www.linear.com/product/LTM2886#packaging for the most recent package drawings.

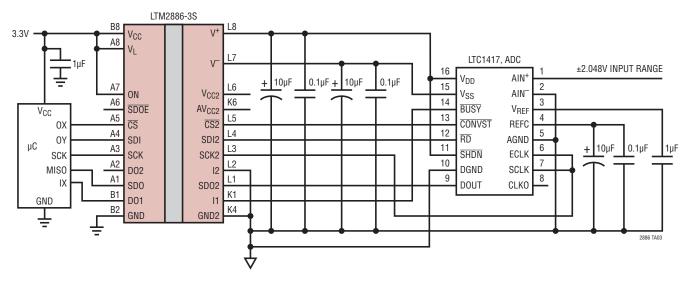


BGA Package 32-Lead (15mm × 11.25mm × 3.42mm) (Reference LTC DWG # 05-08-1851 Rev D)

REVISION HISTORY

REV	DATE	DESCRIPTION	PAGE NUMBER
А	03/17	Added UL-CSA File Number	1
В	07/17	Changed MIN limits for t _{PWU} (SPI and I ² C)	6
		Changed MAX limits for Power-Up Time	6

2886fb



14-Bit Isolated High Speed Bipolar ADC

RELATED PARTS

PART NUMBER	DESCRIPTION	COMMENTS
LTM2881	Isolated RS485/RS422 µModule Transceiver with Integrated DC/DC Converter	20Mbps 2500V _{RMS} Isolation with Power in LGA/BGA Package
LTM2882	Dual Isolated RS232 µModule Transceiver with Integrated DC/DC Converter	2500V _{RMS} Isolation with Power in LGA/BGA Package
LTM2883	SPI/Digital or $I^2C\ \mu Module$ Isolator with Integrated DC/DC Converter	$2500V_{RMS}$ Isolation with Adjustable $\pm 12.5V$ and 5V Power in BGA Package
LTM2884	Isolated USB Transceiver with Power	2500V _{RMS} , Auto Speed Selection, 1 to 2.5W Isolated Power
LTM2889	Isolated CAN FD µModule Transceiver with Power	4Mbps 2500V _{RMS} Isolation with Power in BGA Package
LTM2892	SPI/Digital or I ² C µModule Isolator	3500V _{RMS} Isolation without Power in 9mm × 6.25mm BGA Package
LTC [®] 1535	Isolated RS485 Transceiver	2500V _{RMS} Isolation with External Transformer Drive
LTC4310	Hot-Swappable I ² C Isolators	Bidirectional I ² C Communication, Low Voltage Level Shifting, 100kHz or 400kHz Operation
LTC6803-1, LTC6803-3, LTC6803-2, LTC6803-4	Multicell Battery Stack Monitor	LTC6803-1 Allows for Multiple Devices to be Daisy Chained, the LTC6803-2 Allows for Parallel Communication Battery Stack Topologies





